

Ronald van Langevelde

List of Publications by Citations

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37
papers

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g-index

39
ext. papers

1,917
ext. citations

2.8
avg, IF

3.87
L-index

#	Paper	IF	Citations
37	PSP: An Advanced Surface-Potential-Based MOSFET Model for Circuit Simulation. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 1979-1993	2.9	259
36	Noise modeling for RF CMOS circuit simulation. <i>IEEE Transactions on Electron Devices</i> , 2003 , 50, 618-632	2.9	248
35	Analog circuits in ultra-deep-submicron CMOS. <i>IEEE Journal of Solid-State Circuits</i> , 2005 , 40, 132-143	5.5	235
34	RF-CMOS performance trends. <i>IEEE Transactions on Electron Devices</i> , 2001 , 48, 1776-1782	2.9	204
33	An explicit surface-potential-based MOSFET model for circuit simulation. <i>Solid-State Electronics</i> , 2000 , 44, 409-418	1.7	103
32	Generalizations of the Klaassen-Prins equation for calculating the noise of semiconductor devices. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 2463-2472	2.9	57
31	Effect of gate-field dependent mobility degradation on distortion analysis in MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 1997 , 44, 2044-2052	2.9	56
30	A surface-potential-based high-voltage compact LDMOS transistor model. <i>IEEE Transactions on Electron Devices</i> , 2005 , 52, 999-1007	2.9	46
29	An ultra-low-power 868/915 MHz RF transceiver for wireless sensor network applications 2009 ,		39
28	An advanced explicit surface potential model physically accounting for the quantization effects in deep-submicron MOSFETs. <i>Solid-State Electronics</i> , 2004 , 48, 427-435	1.7	36
27	Benchmark Tests for MOSFET Compact Models With Application to the PSP Model. <i>IEEE Transactions on Electron Devices</i> , 2009 , 56, 243-251	2.9	31
26	The Physical Background of JUNCAP2. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 2098-2107	2.9	29
25	Compact modelling of noise for RF CMOS circuit design. <i>IET Circuits, Devices and Systems</i> , 2004 , 151, 167		24
24	The New CMC Standard Compact MOS Model PSP: Advantages for RF Applications. <i>IEEE Journal of Solid-State Circuits</i> , 2009 , 44, 1415-1424	5.5	20
23	A Unified Nonquasi-Static MOSFET Model for Large-Signal and Small-Signal Simulations. <i>IEEE Transactions on Electron Devices</i> , 2006 , 53, 2035-2043	2.9	20
22	PSP-based compact FinFET model describing dc and RF measurements 2006 ,		19
21	RF Characterization of Schottky Diodes in 65-nm CMOS. <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 1063-1068	2.9	18

20	PSP-SOI: An advanced surface potential based compact model of partially depleted SOI MOSFETs for circuit simulations. <i>Solid-State Electronics</i> , 2009 , 53, 18-29	1.7	16
19	PSP-SOI: A Surface Potential Based Compact Model of Partially Depleted SOI MOSFETs 2007 ,		12
18	A Compact Model for Valence-Band Electron Tunneling Current in Partially Depleted SOI MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2007 , 54, 316-322	2.9	12
17	Benchmarking the PSP Compact Model for MOS Transistors 2007 ,		12
16	Compact modeling of noise in CMOS 2006 ,		12
15	Surface-Potential-Based Compact Model of Bulk MOSFET 2010 , 3-40		10
14	Experimental Demonstration and Modeling of Excess RF Noise in Sub-100-nm CMOS Technologies. <i>IEEE Electron Device Letters</i> , 2010 , 31, 884-886	4.4	9
13	PSP-Based Scalable MOS Varactor Model 2007 ,		8
12	Unified non-quasi-static MOSFET model for large-signal and small-signal simulations		8
11	Advanced Compact MOS Modelling 2001 ,		8
10	Compact modelling of pocket-implanted MOSFETs 2001 ,		6
9	RF Distortion Characterisation of Sub-Micron CMOS 2000 ,		5
8	2019 ,		3
7	Modeling and characterization of noise in 90-nm RF CMOS technology. <i>AIP Conference Proceedings</i> , 2005 ,	0	3
6	(Invited) The new CMC standard compact MOS model PSP: advantages for RF applications 2008 ,		2
5	Compact modeling of noise for RF CMOS circuit simulation 2003 ,		2
4	Noise in DMOS transistors in a BICMOS-technology. <i>IEEE Transactions on Electron Devices</i> , 1996 , 43, 1243-1250	2.1	2
3	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 5246-5253	2.9	1

2 A Robust and Physically Based Compact SOI-LDMOS Model **2002**,

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Parameter Extraction for the PSPHV LDMOS Transistor Model. *IEEE Journal of the Electron Devices Society*, **2020**, 8, 813-824

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